

FORM PTO-1485	SERIAL NO. 10/538,482	CASE NO. 9905/28
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE March 17, 2006	GROUP ART UNIT 2812
(use several sheets if necessary)		APPLICANT(S): Fournel et al.

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
	B1 4,028,149	6/7/1977	Deines et al.		
	B2 5,242,863	9/7/1993	Xiang-Zheng et al.		
	B3 5,300,788	4/5/1994	Fan et al.		
	B4 5,405,802	4/11/1995	Yamagata et al.		
	B5 5,559,043	9/24/1996	Bruel		
	B6 5,811,348	9/22/1998	Matsushita et al.		
	B7 5,854,123	12/29/1998	Sato et al.		
	B8 5,877,070	3/2/1999	Goesele et al.		
	B9 5,909,627	6/1/1999	Egloff		
	B10 5,920,764	7/6/1999	Hanson et al.		
	B11 5,953,622	9/14/1999	Lee et al.		
	B12 5,966,620	10/12/1999	Sakaguchi et al.		
	B13 5,993,677	11/30/1999	Biasse et al.		
	B14 5,994,207	11/30/1999	Henley et al.		
	B15 6,013,563	1/11/2000	Henley et al.		
	B16 6,020,252	2/1/2000	Aspar et al.		
	B17 6,048,411	4/11/2000	Henley et al.		
	B18 6,054,370	4/25/2000	Doyle		
	B19 6,071,795	6/6/2000	Cheung et al.		
	B20 6,103,597	8/15/2000	Aspar et al.		
	B21 6,103,599	8/15/2000	Henley et al.		
	B22 6,127,199	10/3/2000	Inoue		
	B23 6,146,979	11/14/2000	Henley et al.		
	B24 6,150,239	11/21/2000	Goesele et al.		
	B25 6,190,998	2/20/2001	Bruel et al.		
	B26 6,225,190	5/1/2001	Bruel et al.		
	B27 6,225,192	5/1/2001	Aspar et al.		
	B28 6,271,101	8/7/2001	Fukunaga		
	B29 6,303,468	10/16/2001	Aspar et al.		
	B30 6,323,108	11/27/2001	Kub et al.		
	B31 6,323,109	11/27/2001	Okonogi		
	B32 6,346,458	2/12/2002	Bower		
	B33 6,362,077	3/26/2002	Aspar et al.		
	B34 6,513,584	2/4/2003	Bryan et al.		
	B35 6,534,380	3/18/2003	Yamauchi et al.		
	B36 6,593,212	7/15/2003	Kub et al.		
	B37 6,607,969	8/19/2003	Kub et al.		
EXAMINER /Clas Oficial/	DATE CONSIDERED 11/20/2008				

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609;
Draw line through citation if not in conformance and not considered. Include copy of this form with next
communication to applicant.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /E.U./

FORM PTO-1449	SERIAL NO. 10/538,482	CASE NO. 9905/28
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE March 17, 2006	GROUP ART UNIT 2812
(use several sheets if necessary)	APPLICANT(S): Fourenel et al.	

Page 2 of 4

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
	B38 6,727,549	4/27/2004	Doyle		
	B39 6,756,286	6/29/2004	Moriceau et al.		
	B40 6,770,507	8/3/2004	Abe et al.		
	B41 6,946,365	9/20/2005	Aspar et al.		
	B42 2002/0025604	2/28/2002	Tiwari		
	B43 2002/0153563	10/24/2002	Ogura		
	B44 2002/0185684	12/12/2002	Campbell et al.		
	B45 2003/0077885	4/24/2003	Aspar et al.		
	B46 2003/0134489	7/17/2003	Schwarzenbach et al.		
	B47 2003/0162367	8/28/2003	Roche		
	B48 2003/0199105	10/23/2003	Kub et al.		
	B49 2004/0144487	7/29/2004	Martinez et al.		

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO
	B50 EP 0 293 049 B1	9/29/1993	Europe		
	B51 EP 0 533 551 B1	3/9/2000	Europe		Abstract
	B52 EP 0 717 437 B1	4/24/2002	Europe		
	B53 EP 0 767 486 B1	1/2/2004	Europe		
	B54 EP 0 786 801A1	6/18/2003	Europe		Abstract
	B55 EP 0 793 263 A2	9/3/1997	Europe		
	B56 EP 0 801 419 A1	10/15/1997	Europe		Abstract
	B57 EP 0 807 970 A1	11/19/1997	Europe		Abstract
	B58 EP 0 902 843 B1	3/29/2000	Europe		Abstract
	B59 EP 0 917 193 A1	5/19/1999	Europe		
	B60 EP 0 925 888 B1	11/10/2004	Europe		
	B61 EP 0 938 129 A1	8/25/1999	Europe		
	B62 EP 0 994 503 A1	4/19/2000	Europe		Abstract
	B63 EP 1 014 452 B1	5/3/2006	Europe		
	B64 FR 2 748 850 A1	11/21/1997	France		Abstract
	B65 FR 2 748 851	11/21/1997	France		Abstract
	B66 FR 2 758 907 A1	7/31/1998	France		Abstract
	B67 FR 2 767 416 A1	2/19/1999	France		Abstract
	B68 FR 2 773 261	7/2/1999	France		Abstract
	B69 FR 2 774 510 A1	8/6/1999	France		Abstract
	B70 FR 2 781 925 A1	2/4/2000	France		Abstract
	B71 FR 2 796 491	1/19/01	France		Abstract

EXAMINER	DATE CONSIDERED
----------	-----------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/538,482	CASE NO. 9905/28
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE March 17, 2006	GROUP ART UNIT 2812
(use several sheets if necessary)	APPLICANT(S): Fourenel et al.	

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO
	B72 FR 2 797 347	2/9/2001	France		Abstract
	B73 FR 2 809 867	12/7/2001	France		Abstract
	B74 FR 2 847 075 A1	5/14/2004	France		Abstract
	B75 JP 62265717	11/18/1987	Japan		Abstract
	B76 JP 07-254690	10/3/1995	Japan		Abstract
	B77 JP 7-302889	11/14/1995	Japan		Abstract
	B78 JP 09-213594	8/15/1997	Japan		Abstract
	B79 JP 09-307719	11/28/1997	Japan		Abstract
	B80 JP 11045862	2/16/1999	Japan		Abstract
	B81 JP 11074208	3/16/1999	Japan		Abstract
	B82 JP 11-87668	3/30/1999	Japan		Abstract
	B83 JP 11-145436	5/28/1999	Japan		Abstract
	B84 JP 11-233449	8/27/1999	Japan		Abstract
	B85 WO 99/08316	2/18/1999	WIPO		Abstract
	B86 WO 99/35674 A1	7/15/1999	WIPO		Abstract
	B87 WO 99/39378	8/5/1999	WIPO		
	B88 WO 00/63965	10/26/2000	WIPO		
	B89 WO 01/11930A2	2/15/2001	WIPO		
	B90 WO 02/47156 A1	6/13/2002	WIPO		Abstract
	B91 WO 02/083387 A1	10/24/2002	WIPO		Abstract
	B92 WO 03/013815	2/20/2003	WIPO		Abstract
	B93 WO 04/044976	5/27/2004	WIPO		Abstract

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS <small>(Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)</small>
B94	Agarwal et al "Efficient production of Silicon-on-insulator films by co-implantation of HE ⁺ with H ⁺ ", <i>Applied Physics Letter</i> , <i>American Institute of Physics</i> , Vol. 72, No. 9, March 1998, pp. 1086-1088
B95	Bruehl et al., [Vol. 99-1] Meeting Abstract No. 333, "Single-crystal semiconductor layer delamination and transfer through hydrogen implantation," <i>The 195th Meeting of The Electrochemical Society</i> , May 2-6, 1999, Seattle, Washington
B96	Camperi-Ginestet et al., "Alignable Epitaxial Liftoff of GaAs Materials with Selective Deposition Using Polyimide Diaphragms", <i>IEEE Transactions Photonics Technology Letters</i> , Vol. 3, No. 12, December 1991, pp. 1123-1126
B97	Cerofolini et al. "Ultradense Gas Bubbles in Hydrogen-or-Helium-Implanted (or Co-implanted) Silicon", <i>Materials Science and Engineering</i> , B71, 2000, pp. 196-202

EXAMINER	/Elias Ullah/	DATE CONSIDERED	11/20/2006
----------	---------------	-----------------	------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449	SERIAL NO. 10/538,482	CASE NO. 9905/28
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE March 17, 2006	GROUP ART UNIT 2812
(use several sheets if necessary)		APPLICANT(S): Fourenel et al.

Page 4 of 4

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
B98	Demeester, et al., "Epitaxial Lift-off and its Applications", <i>Semicond. Sci. Technol.</i> , Vol. 8, 1993, pp. 1124-1135
B99	DiCioccio et al., "III-V layer transfer onto silicon and applications", <i>Phys. Stat. Sol. (a)</i> , Vol. 202, No. 4, 2005, pp. 509-515/DOI 10.1002/pssa. 200460411
B100	Hamaguchi, et al., "Novel LSI/SOI Wafer Fabrication Using Device Layer Transfer Technique" <i>Proc. IEDM</i> , 1985, pp. 688-691
B101	Henttinen et al., "Mechanically induced Si Layer Transfer in Hydrogen-Implanted Si-Wafers", <i>American Institute of Physics</i> , Vol. 76, No. 17, April 2000, pp. 2370-2372
B102	Kucheyev et al., "Ion implantation into GaN", <i>Materials Science and Engineering</i> , 33, 2001, pp. 51-107
B103	Liu et al., "Ion implantation in GaN at liquid-nitrogen temperature: Structural characteristics and amorphization," <i>Physical Review B of The American Physical Society</i> , Vol. 57, No. 4, 1988, pp. 2530-2535
B104	Moriceau et al., [Vol. 99-1] Meeting Abstract No. 405, "A New Characterization Process Used to Qualify SOI Films," <i>The 195th Meeting of The Electrochemical Society</i> , May 2-6, 1999, Seattle, Washington.
B105	Pollentier et al., "Fabrication of High-Radiance LEDs by Epitaxial Lift-off" <i>SPIE</i> , Vol. 1361, 1990, pp. 1056-1062
B106	Suzuki et al., "High-Speed and Low Power n ⁺ -p ⁺ Double-Gate SOI CMOS", <i>IEICE Trans. Electron.</i> , Vol. E78-C, No. 4, April 1995, pp. 360-367
B107	Tong et al., "Low Temperature Si Layer Splitting", <i>Proceedings 1997 IEEE International SOI Conference</i> , Oct. 1997, pgs. 126-127
B108	Wong et al., "Integration of GaN Thin Films with Dissimilar Substrate Materials by Pd-In Metal Bonding and Laser Lift-off", <i>Journal of Electronic Materials</i> , Vol. 28, No. 12, 1999, pp. 1409-1413
B109	Yun et al., "Fractional Implantation Area Effects on Patterned Ion-Cut Silicon Layer Transfer," Dept. of Electrical Eng. And Computer Sciences, University of California, Berkeley, CA 94720, USA, 1999 IEEE International SOI Conference, Oct. 1999, pp. 129-30
B110	Yun et al., "Thermal and Mechanical Separations of Silicon Layers from Hydrogen Pattern-Implanted Wafers," <i>Journal of Electronic Materials</i> , Vol. No. 36, No. 8 2001

EXAMINER	/Elias Ullah	DATE CONSIDERED	11/20/2008
----------	--------------	-----------------	------------

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Appln. of: FURNEL ET AL.

Appln. No.: 10/538,482

Filed: March 17, 2006

For: METHOD FOR MAKING A
STRESSED STRUCTURE
DESIGNED TO BE
DISSOCIATED

Examiner: Lebentritt, Michael

Art Unit: 2812

Attorney Docket No: 9905/28

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

In accordance with the duty of disclosure under 37 C.F.R. §1.56 and §§1.97-1.98, and more particularly in accordance with 37 C.F.R. §1.97(b), Applicants hereby cite the following reference(s):

DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	NAME
4,028,149	6/7/1977	Deines et al.
5,242,863	9/7/1993	Xiang-Zheng et al.
5,300,788	4/5/1994	Fan et al.
5,405,802	4/11/1995	Yamagata et al.
5,559,043	9/24/1996	Bruei
5,811,348	9/22/1998	Matushita et al.
5,854,123	12/29/1998	Sato et al.
5,877,070	3/2/1999	Goesele et al.
5,909,627	6/1/1999	Egloff
5,920,764	7/6/1999	Hanson et al.
5,953,622	9/14/1999	Lee et al.
5,966,620	10/12/1999	Sakaguchi et al.
5,993,677	11/30/1999	Blasse et al.
5,994,207	11/30/1999	Henley et al.
6,013,563	1/11/2000	Henley et al.
6,020,252	2/1/2000	Aspar et al.
6,048,411	4/11/2000	Henley et al.
6,054,370	4/25/2000	Doyle
6,071,795	6/6/2000	Cheung et al.
6,103,597	8/15/2000	Aspar et al.
6,103,599	8/15/2000	Henley et al.
6,127,199	10/3/2000	Inoue
6,146,979	11/14/2000	Henley et al.
6,150,239	11/21/2000	Goesele et al.

DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	NAME
6,190,998	2/20/2001	Bruel et al.
6,225,190	5/1/2001	Bruel et al.
6,225,192	5/1/2001	Aspar et al.
6,271,101	8/7/2001	Fukunaga
6,303,468	10/16/2001	Aspar et al.
6,323,108	11/27/2001	Kub et al.
6,323,109	11/27/2001	Okonogi
6,346,458	2/12/2002	Bower
6,362,077	3/26/2002	Aspar et al.
6,513,564	2/4/2003	Bryan et al.
6,534,380	3/18/2003	Yamauchi et al.
6,593,212	7/15/2003	Kub et al.
6,607,969	8/19/2003	Kub et al.
6,727,549	4/27/2004	Doyle
6,756,286	6/29/2004	Moriceau et al.
6,770,507	8/3/2004	Abe et al.
6,946,365	9/20/2005	Aspar et al.
2002/0025604	2/28/2002	Tiwari
2002/0153563	10/24/2002	Ogura
2002/0185684	12/12/2002	Campbell et al.
2003/0077885	4/24/2003	Aspar et al.
2003/0134489	7/17/2003	Schwarzenbach et al.
2003/0162367	8/28/2003	Roche
2003/0199105	10/23/2003	Kub et al.
2004/0144487	7/29/2004	Martinez et al.

FOREIGN DOCUMENTS

DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	COUNTRY
EP 0 293 049 B1	9/29/1993	Europe
EP 0 533 551 B1	3/9/2000	Europe
EP 0 717 437 B1	4/24/2002	Europe
EP 0 767 486 B1	1/2/2004	Europe
EP 0 786 801A1	6/18/2003	Europe
EP 0 793 263 A2	9/3/1997	Europe
EP 0 801 419 A1	10/15/1997	Europe
EP 0 807 970 A1	11/19/1997	Europe
EP 0 902 843 B1	3/29/2000	Europe
EP 0 917 193 A1	5/19/1999	Europe
EP 0 925 888 B1	11/10/2004	Europe
EP 0 938 129 A1	8/25/1999	Europe
EP 0 994 503 A1	4/19/2000	Europe
EP 1 014 452 B1	5/3/2006	Europe
FR 2 748 850 A1	11/21/1997	France
FR 2 748 851	11/21/1997	France

DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	COUNTRY
FR 2 758 907 A1	7/31/1998	France
FR 2 767 416 A1	2/19/1999	France
FR 2 773 261	7/2/1999	France
FR 2 774 510 A1	8/6/1999	France
FR 2 781 925 A1	2/4/2000	France
FR 2 796 491	1/19/01	France
FR 2 797 347	2/9/2001	France
FR 2 809 867	12/7/2001	France
FR 2 847 075 A1	5/14/2004	France
JP 62265717	11/18/1987	Japan
JP 07-254690	10/3/1995	Japan
JP 7-302889	11/14/1995	Japan
JP 09-213594	8/15/1997	Japan
JP 09-307719	11/28/1997	Japan
JP 11045862	2/16/1999	Japan
JP 11074208	3/16/1999	Japan
JP 11-87668	3/30/1999	Japan
JP 11-145436	5/28/1999	Japan
JP 11-233449	8/27/1999	Japan
WO 99/08316	2/18/1999	WIPO
WO 99/35674 A1	7/15/1999	WIPO
WO 99/39378	8/5/1999	WIPO
WO 00/63965	10/26/2000	WIPO
WO 01/11930A2	2/15/2001	WIPO
WO 02/47156 A1	6/13/2002	WIPO
WO 02/083387 A1	10/24/2002	WIPO
WO 03/013815	2/20/2003	WIPO
WO 04/044976	5/27/2004	WIPO

OTHER DOCUMENTS

Agarwal et al "Efficient production of Silicon-on-insulator films by co-implantation of HE ⁺ with H ⁺ ", <i>Applied Physics Letter</i> , <i>American Institute of Physics</i> , Vol. 72, No. 9, March 1998, pp. 1086-1088
Bruel et al., [Vol. 99-1] Meeting Abstract No. 333, "Single-crystal semiconductor layer delamination and transfer through hydrogen implantation," <i>The 195th Meeting of The Electrochemical Society</i> , May 2-6, 1999, Seattle, Washington
Camperi-Ginestet et al., "Alignable Epitaxial Liftoff of GaAs Materials with Selective Deposition Using Polyimide Diaphragms", <i>IEEE Transactions Photonics Technology Letters</i> , Vol. 3, No. 12, December 1991, pp. 1123-1126
Cerofolini et al. "Ultradense Gas Bubbles in Hydrogen-or-Helium-Implanted (or Co-implanted) Silicon", <i>Materials Science and Engineering</i> , B71, 2000, pp. 196-202
Demeester, et al., "Epitaxial Lift-off and its Applications", <i>Semicond. Sci. Technol.</i> , Vol. 8, 1993, pp. 1124-1135
DiCioccio et al., "III-V layer transfer onto silicon and applications", <i>Phys. Stat. Sol. (a)</i> , Vol. 202, No. 4., 2005, pp. 509-515/DOI 10.1002/pssa.200460411
Hamaguchi, et al., "Novel LSI/SOI Wafer Fabrication Using Device Layer Transfer Technique" <i>Proc. IEDM</i> , 1985, pp. 688-691

Henttinen et al. "Mechanically induced Si Layer Transfer in Hydrogen-Implanted Si-Wafers", <i>American Institute of Physics</i> , Vol. 76, No. 17, April 2000, pp. 2370-2372
Kucheyev et al., "Ion implantation into GaN", <i>Materials Science and Engineering</i> , 33, 2001, pp. 51-107
Liu et al., "Ion implantation in GaN at liquid-nitrogen temperature: Structural characteristics and amorphization," <i>Physical Review B of The American Physical Society</i> , Vol. 57, No. 4, 1988, pp. 2530-2535
Moriceau et al., [Vol. 99-1] Meeting Abstract No. 405, "A New Characterization Process Used to Qualify SOI Films," <i>The 195th Meeting of The Electrochemical Society</i> , May 2-6, 1999, Seattle, Washington.
Pollentier et al., "Fabrication of High-Radiance LEDs by Epitaxial Lift-off" <i>SPIE</i> , Vol. 1361, 1990, pp. 1056-1062
Suzuki et al., "High-Speed and Low Power n ⁻ -p ⁺ Double-Gate SOI CMOS", <i>IEICE Trans. Electron.</i> , Vol. E78-C, No. 4, April 1995, pp. 360-367
Tong et al., "Low Temperature Si Layer Splitting", <i>Proceedings 1997 IEEE International SOI Conference</i> , Oct. 1997, pgs. 126-127
Wong et al., "Integration of GaN Thin Films with Dissimilar Substrate Materials by Pd-In Metal Bonding and Laser Lift-off", <i>Journal of Electronic Materials</i> , Vol. 28, No. 12, 1999, pp. 1409-1413
Yun et al., "Fractional Implantation Area Effects on Patterned Ion-Cut Silicon Layer Transfer," Dept. of Electrical Eng. And Computer Sciences, University of California, Berkeley, CA 94720, USA, 1999 IEEE International SOI Conference, Oct. 1999, pg. 129-30
Yun et al., "Thermal and Mechanical Separations of Silicon Layers from Hydrogen Pattern-Implanted Wafers," <i>Journal of Electronic Materials</i> , Vol. No. 36, No. 8 2001

Applicants are enclosing Form PTO-1449 (four sheets), along with a copy of each listed reference for which a copy is required under 37 C.F.R. §1.98(a)(2). As each of the listed references is in English, no further commentary is believed to be necessary, 37 C.F.R. §1.98(a)(3). Applicants respectfully request the Examiner's consideration of the above reference(s) and entry thereof into the record of this application.

By submitting this Statement, Applicants are attempting to fully comply with the duty of candor and good faith mandated by 37 C.F.R. §1.56. As such, this Statement is not intended to constitute an admission that any of the enclosed references, or other information referred to therein, constitutes "prior art" or is otherwise "material to patentability," as that phrase is defined in 37 C.F.R. §1.56(a).

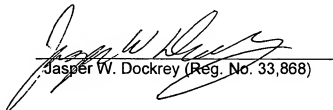
Appln. No. 10/538,482Attorney Docket No. 9905/28

Applicants have calculated no fee to be due in connection with the filing of this Statement. However, the Director is authorized to charge any fee deficiency associated with the filing of this Statement to a deposit account, as authorized in the Transmittal accompanying this Statement.

Respectfully submitted,

December 4, 2006

Date


Jasper W. Dockrey (Reg. No. 33,868)